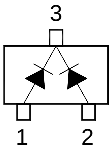
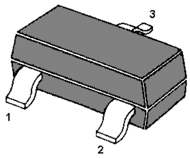
SB425D

Silicon Epitaxial Planar Schottky Barrier Diode

Low current rectification





Marking Code: "**YA**"
TO-236 Plastic Package

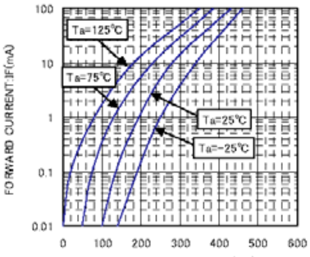
Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RM}	40	V
Reverse Voltage	V_R	40	V
Average Rectified Forward Current [1]	$I_{F(AV)}$	100	mA
Peak Forward Surge Current (60 Hz 1 Cycle) [1]	I_{FSM}	1	A
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	- 55 to + 125	°C

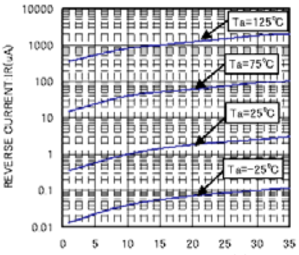
[1] Rating of per diode

Characteristics at T_a = 25 °C

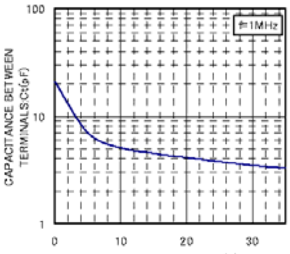
Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at I_F = 10 mA at I_F = 100 mA	V_F	- -	0.34 0.55	V
Reverse Current at V_R = 10 V	I_R	-	30	µA
Capacitance between Terminals at V_R = 10 V, f = 1 MHz	C_t	6	-	pF



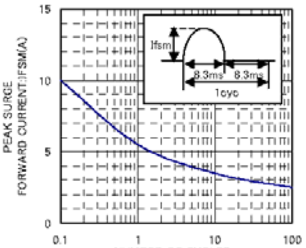
VF-IF CHARACTERISTICS



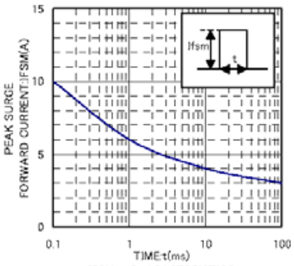
VR-IR CHARACTERISTICS



VR-Ct CHARACTERISTICS



IFSM-CYCLE CHARACTERISTICS



IFSM-t CHARACTERISTICS

Dated : 04/08/2007